	Type	#	Hits	Search Text	DBs
⊢	BRS	1.1	120	recharge near period	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS		13371	gate near pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	ГЗ	248744	low near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	Г4	0	1 and 2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	1.5	4	1 and 2	
9	BRS	91	1167	345/204.ccls.	us- o;
7	BRS	17	1532	345/211-213.ccls.	US- PO; B
8	BRS	Г8	4417	345/87-92.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
0	BRS	61	6814	6 or 7 or 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	178	increase and (recharging adj time)	US- PO; B
11	BRS	L11	0	9 and 10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L12	2557	transistor and (temperature near characteristic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

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	Type	# 7	Hits	Search Text	DBs
13	BRS	L13	22561	recharging	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14 .	36	12 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	109665	rcD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	10	1 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L17	9833	TFT and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L18	401	recharging adj time	USPAT; US-PGPUB; adj time EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	·	17 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	# 1	Hits	Search Text	DBs
1	BRS	L1	120	recharge near period	-sn
2	BRS	1.2	13371	gate near pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	Г.3	248744	low near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	0	1 and 2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
5	BRS	L5	4	1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	97	1167	345/204.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	1.7	1532	345/211-213.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS		4417	345/87-92.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L9	6814	6 or 7 or 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	178	increase and (recharging adj time)	JS-
11	BRS	L11	0	9 and 10	US- 20;
12	BRS	L12	2557	transistor and (temperature near characteristic)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	#	Hits	Search Text	DBs
13	BRS	ь13	22561	recharging	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L14	36	12 and 13	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L15	109665	LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L16	10	1 and 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
17	BRS	L17	9833	TFT and LCD	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L:18	401	recharging adj time	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
19	BRS	L19	1	17 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L20	448	circuit near recharge	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	L21	E	3 and 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	# H	Hits	Search Text	DBs
Ţ	BRS	L1	120	recharge near period	US-
2	BRS	1.2	13371	gate near pulse	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	Г.3	248744	low near temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
4	BRS	L4	0	1 and 2 and 3	US- PO;
5	BRS	Г.5	4	1 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	BRS	Lб	1167	345/204.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	1.7	1532	345/211-213.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	Г8	4417	345/87-92.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	L9	6814	6 or 7 or 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	BRS	L10	178	increase and (recharging adj time)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	BRS	L11	0	9 and 10	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB